Complementary ThermalTrak[™] Transistors

The ThermalTrak family of devices has been designed to eliminate thermal equilibrium lag time and bias trimming in audio amplifier applications. They can also be used in other applications as transistor die protection devices.

Features

- Thermally Matched Bias Diode
- Instant Thermal Bias Tracking
- Absolute Thermal Integrity
- High Safe Operating Area
- Pb–Free Packages are Available*

Benefits

- Eliminates Thermal Equilibrium Lag Time and Bias Trimming
- Superior Sound Quality Through Improved Dynamic Temperature Response
- Significantly Improved Bias Stability
- Simplified Assembly
 - Reduced Labor Costs
 - Reduced Component Count
- High Reliability

Applications

- High-End Consumer Audio Products
 - Home Amplifiers
 - Home Receivers
- Professional Audio Amplifiers
 - Theater and Stadium Sound Systems
 - Public Address Systems (PAs)



ON Semiconductor®

http://onsemi.com

BIPOLAR POWER TRANSISTORS 15 AMP, 260 VOLT, 180 WATT



TO-264, 5 LEAD CASE 340AA STYLE 1

MARKING DIAGRAM

SCHEMATIC



NJL0xxxD = Device Code

	xxx = 281 or 302
G	= Pb-Free Package
A	= Assembly Location
YY	= Year
WW	=Work Week

ORDERING INFORMATION

Device	Package	Shipping
NJL0281D	TO-264	25 Units / Rail
NJL0281DG	TO-264 (Pb-Free)	25 Units / Rail
NJL0302D	TO-264	25 Units / Rail
NJL0302DG	TO-264 (Pb-Free)	25 Units / Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS (T_J = $25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	V _{CEO}	260	Vdc	
Collector-Base Voltage	V _{CBO}	260	Vdc	
Emitter-Base Voltage	V _{EBO}	5	Vdc	
Collector-Emitter Voltage - 1.5 V	V _{CEX}	260	Vdc	
Collector Current – Continuous – Peak (Note 1)	I _C	15 25	Adc	
Base Current – Continuous	I _B	1.5	Adc	
Total Power Dissipation @ $T_C = 25^{\circ}C$ Derate Above 25°C	PD	180 1.43	W ₩/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	– 65 to +150	°C	
DC Blocking Voltage	V _R	200	V	
Average Rectified Forward Current	I _{F(AV)}	1.0	А	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Case	$R_{ extsf{ heta}JC}$	0.694	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.

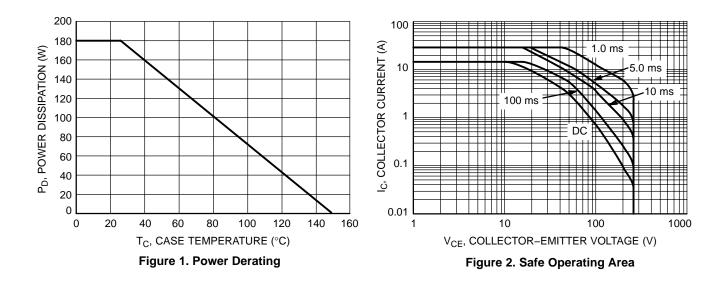
ATTRIBUTES

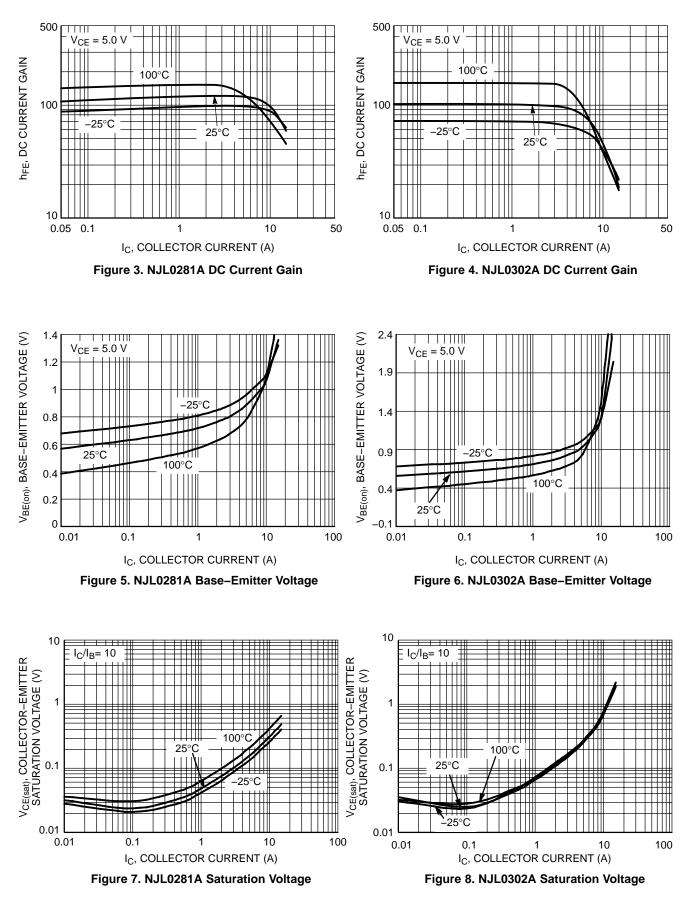
	Characteristic	Value
ESD Protection	Human Body Model Machine Model	>8000 V > 400 V
Flammability Rating		UL 94 V–0 @ 0.125 in

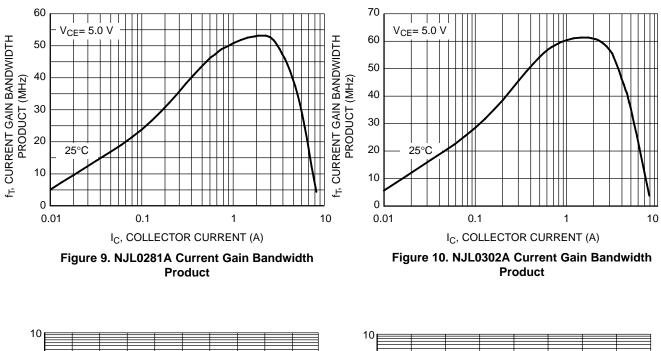
ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage $(I_C = 100 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	260	_	Vdc
Collector Cutoff Current ($V_{CB} = 260 \text{ Vdc}, I_E = 0$)	I _{CBO}	_	10	μAdc
Emitter Cutoff Current ($V_{EB} = 5 \text{ Vdc}, I_C = 0$)	I _{EBO}	_	5	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 500 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}$) ($I_C = 1 \text{ Adc}, V_{CE} = 5 \text{ Vdc}$) ($I_C = 3 \text{ Adc}, V_{CE} = 5 \text{ Vdc}$)	h _{FE}	75 75 75	150 150 150	
Collector–Emitter Saturation Voltage $(I_C = 5 \text{ Adc}, I_B = 0.5 \text{ Adc})$	V _{CE(sat)}		1.0	Vdc
Base–Emitter On Voltage (I _C = 5 Adc, V _{CE} = 5 Vdc)		_	1.2	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product ($I_C = 1 \text{ Adc}, V_{CE} = 5 \text{ Vdc}, f_{test} = 1 \text{ MHz}$)	f _T	30	_	MHz
Output Capacitance (V_{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)	C _{ob}	_	400	pF
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 1.0 \text{ A}, T_J = 25^{\circ}\text{C}$) ($i_F = 1.0 \text{ A}, T_J = 150^{\circ}\text{C}$)	VF	1.1 0.93		V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 150^{\circ}C$)	i _R	10 100		μΑ
Maximum Reverse Recovery Time (i _F = 1.0 A, di/dt = 50 A/μs)	t _{rr}	1	00	ns

2. Diode Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.







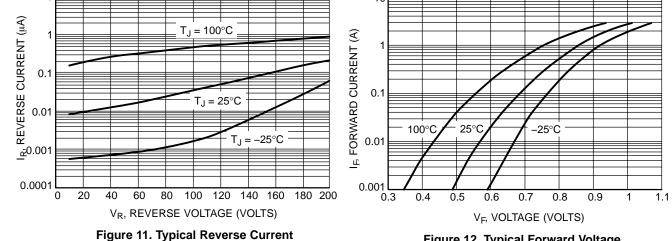
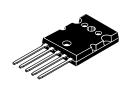


Figure 12. Typical Forward Voltage

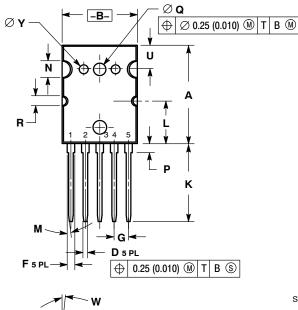
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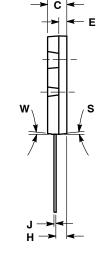
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SCALE 1:2





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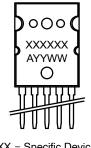
TO-264, 5 LEAD CASE 340AA-01 ISSUE O

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR 4. ANODE 5. CATHODE

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES	;	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	25.857	25.984	26.111	1.018	1.023	1.028
в	19.761	19.888	20.015	0.778	0.783	0.788
С	4.699	4.890	5.182	0.185	0.199	0.204
D	1.	219 BS	C	0.	0480 BS	SC
Е	1.890	2.042	2.184	0.0748	0.0804	0.0860
F	1.981 BSC 0.0780 BSC		SC			
G	3	3.81 BSC		0.150 BSC		С
н	2.667	2.718	2.769	0.1050	0.1070	0.1090
J	0.584 BSC		0.0230 BSC			
к	20.422	20.549	20.676	0.804	0.809	0.814
L	1	1.28 RE	F	C	.444 RE	F
Μ	0 °		7 °	0 °		7 °
Ν		4.57 REF			0.180 R	EF
Р	2.259	2.386	2.513	0.0889	0.0939	0.0989
Q	3.480 BSC		0	.1370 B	SC	
R	2.54 REF			0.100 RE		
S	0 °		8 °	0 °		8 °
U	6.17 REF			0.243 R	EF	
W	0 °		6 °	0 °		6 °
Υ	2.388 BSC		SC	0	.0940 B	SC

GENERIC **MARKING DIAGRAM***



XXXXXX = Specific Device Code А

- = Assembly Location
- YΥ = Year
- WW = Work Week
- = Pb-Free Package G or •
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

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